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I hereby certify that on the date specified below, this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

September 25, 2007 ABeggs
Date Alexandra Beggs

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Kie Ahn and Leonard Forbes Attorney Docket No.: 501306.01
Patent No. : US 6,989,573 B2
Issued : January 24, 2006
Title : LANTHANIDE OXIDE/ZIRCONIUM OXIDE ATOMIC LAYER DEPOSITED NANOLAMINATE GATE DIELECTRICS

NOTIFICATION OF ERRORS

Certificate
NOV 09 2007
of Correction

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following errors were noted in a review of the above-identified letters patent. One or more of these errors was inadvertently made in the original application, while the others occurred in the printing of the patent. Since the errors are of an obvious nature, a formal Certificate of Correction is not believed to be warranted at this time. Therefore, applicants requests that this notification be placed in the Patent and Trademark Office file.

Column, Line	Reads	Should Read
Item (56), Jeon Reference, Line 4	"to474."	--to 474.--
Item (56), First Kukli Reference	"Kukli, Kaupo, et al., "*Influence of thickness and growth temperature one the*	--Kukli, Kaupo, et al., "*Influence of thickness and growth temperature on the properties of*

	properties of zirconium oxide films grown by atomic layer deposition on silicon," Thin Solid Films 410, 2002, pp. 53-60."	*zirconium oxide films grown by atomic layer deposition on silicon,*" Thin Solid Films 410, 2002, pp. 53-60.--
Column 1, Line 28	"used gate dielectrics, SiO_2,"	--used gate dielectrics, SiO_2,--
Column 1, Line 46	"may cause fringing-field"	--may cause a fringing-field--
Column 1, Line 48	"dielectric constant"	--dielectric constants--
Column 1, Line 65	"to have exhibit a relative"	--to have exhibited a relative--
Column 2, Line 5	"hafnium oxide (Ta_2O5-HfO_2),"	--hafnium oxide (Ta_2O_5-HfO_2),"
Column 2, Line 46	"of doped zinc sulfide an alkaline earth metal"	--of doped zinc sulfide and alkaline earth metal--
Column 2, Line 49	"and nitride firms in composite multiplaner"	--and nitride films in composite multiplanar--
Column 3, Line 13	"to about 6 m"	--to about 6 nm--
Column 3, Line 29	"layer is formed RS-ALD"	--layer is formed by RS-ALD--
Column 3, Lines 48 and 57	"embodiment of semiconductor"	--embodiment of a semiconductor--
Column 3, Line 66	"form the transistor the laminate"	--form the transistor of the laminate--
Column 5, Line 19	"as describe hereafter."	--as described hereafter.--
Column 5, Line 34	"embodiment of invention."	--embodiment of the invention.--
Column 5, Line 36	"in a substrate **46** a gate"	--in a substrate **46**, a gate--
Column 6, Line 15	"or Cr, or suicides"	--or Cr, or silicides--
Column 6, Line 51	"onto and appropriate"	--onto appropriate--
Column 6, Lines 52 and 55	"herein after."	--hereinafter.--
Column 7, Line 4	"by, for example, by Wen-Jie Qi,"	--by, for example, Wen-Jie Qi,--
Column 7, Line 8	"ambient atmospheres."	--ambient atmosphere.--

Column 8, Line 53	"thickness made the foregoing method"	--thickness made in the foregoing method--
Column 10, Line 31	"a second electrode, and"	--a second electrode; and--
Column 10, Line 64	"and a drain region, and"	--and a drain region; and--
Column 12, Line 45	" a second electrode, and"	--a second electrode; and--
Column 13, Line 9	"a second electrode, and"	--a second electrode; and--
Column 13, Line 42	"drain region, and"	--drain region; and--
Column 14, Line 65	"a second electrode, and"	--a second electrode; and--
Column 15, Line 29	"drain region, and"	--drain region; and--

Respectfully submitted,

Date: Sept. 24, 2007

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